1A, 200V-1000V High Efficient Surface Mount Rectifier

FEATURES

- AEC-Q101 qualified
- Glass passivated junction chip
- Ideal for automated placement
- Low power loss, high efficiency
- Fast switching for high efficiency
- Low profile package
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Freewheeling
- Snubber
- DC/DC converters
- Automotive application

MECHANICAL DATA

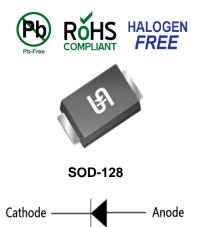
- Case: SOD-128
- Molding compound meets UL 94V-0 flammability rating
- Moisture sensitivity level: level 1, per J-STD-020

- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.028g (approximately)

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	HS1DFSH	HS1GFSH	HS1JFSH	HS1KFSH	HS1MFSH	UNIT
Marking code on the device			HS1DFH	HS1GFH	HS1JFH	HS1KFH	HS1MFH	
Repetitive peak reverse voltage		V _{RRM}	200	400	600	800	1000	V
Reverse voltage, total rms value		V _{R(RMS)}	140	280	420	560	700	V
Forward current		I _F	1					А
Surge peak forward current, single half sine-wave	t = 8.3ms				35			А
superimposed on rated load	t = 1.0ms	I _{FSM}			90			А
Junction temperature		TJ	-55 to +150				°C	
Storage temperature		T _{STG}	-55 to +150					°C

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KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
١ _F	1	А		
V _{RRM}	200-1000	V		
I _{FSM}	35	А		
T _{J MAX}	150	°C		
Package	SOD-128			
Configuration	Single Die			







THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ТҮР	UNIT	
Junction-to-lead thermal resistance	R _{ejl}	29	°C/W	
Junction-to-ambient thermal resistance	R _{eja}	51	°C/W	
Junction-to-case thermal resistance	R _{eJC}	22	°C/W	

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	ΤΥΡ	MAX	UNIT
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.80	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		0.85	1.00	V
	HS1DFSH	$I_F = 0.5A, T_J = 125^{\circ}C$		0.65	-	V
		I _F = 1.0A, T _J = 125°C		0.71	0.80	V
		$I_F = 0.5A, T_J = 25^{\circ}C$		0.84	-	V
	HS1GFSH	$I_F = 1.0A, T_J = 25^{\circ}C$	-	0.91	1.30	V
	naigran	$I_F = 0.5A, T_J = 125^{\circ}C$		0.68	-	V
Forward voltage ⁽¹⁾		$I_F = 1.0A, T_J = 125^{\circ}C$.,	0.76	0.86	V
Forward vollage		$I_F = 0.5A, T_J = 25^{\circ}C$	V _F	0.92	-	V
	HS1JFSH	$I_F = 1.0A, T_J = 25^{\circ}C$		1.02	1.70	V
	HS IJF SH	$I_F = 0.5A, T_J = 125^{\circ}C$		0.73	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		0.83	1.02	V
	HS1KFSH HS1MFSH	$I_F = 0.5A, T_J = 25^{\circ}C$		1.32	-	V
		$I_F = 1.0A, T_J = 25^{\circ}C$		1.49	1.70	V
		$I_F = 0.5A, T_J = 125^{\circ}C$		0.98	-	V
		$I_F = 1.0A, T_J = 125^{\circ}C$		1.16	1.39	V
$\mathbf{r} = \mathbf{r} + $		$T_J = 25^{\circ}C$	1	-	1	μA
Reverse current @ rated $V_R^{(2)}$		T _J = 125°C	I _R	-	35	μA
	HS1DFSH HS1GFSH	I _F = 0.5A, I _R = 1.0A, Irr = 0.25A	t _{rr}	-	50	ns
Reverse recovery time	HS1JFSH HS1KFSH HS1MFSH			-	75	ns
	HS1DFSH		CJ	20	-	pF
	HS1GFSH]		17	-	pF
Junction capacitance	HS1JFSH	1MHz, V _R = 4.0V		13	-	pF
	HS1KFSH HS1MFSH			8	-	pF

Notes:

(1) Pulse test with PW = 0.3ms

(2) Pulse test with PW = 30ms



ORDERING INFORMATION

ORDERING CODE ⁽¹⁾	PACKAGE	PACKING		
HS1xFSH M3G	SOD-128	3,500 / 7" reel		
HS1xFSH M2G	SOD-128	14,000 / 13" reel		

Notes:

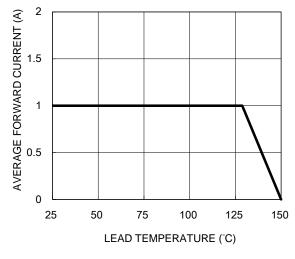
(1) "x" defines voltage from 200V(HS1DFSH) to 1000V(HS1MFSH)



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

Fig.1 Forward Current Derating Curve





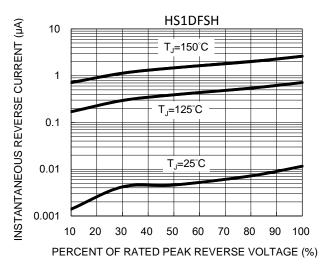


Fig.5 Typical Reverse Characteristics

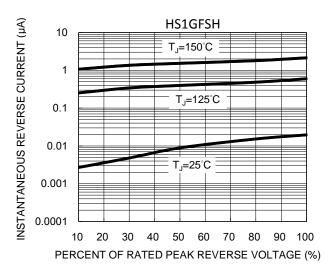


Fig.2 Typical Junction Capacitance

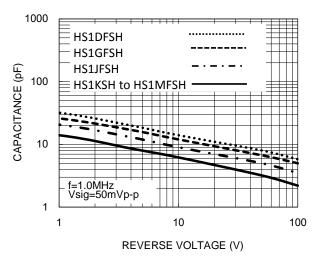


Fig.4 Typical Forward Characteristics

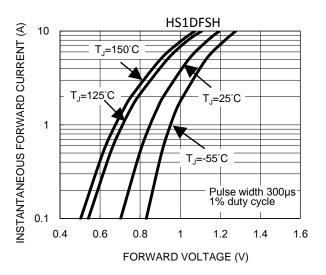
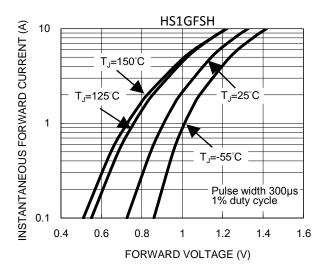


Fig.6 Typical Forward Characteristics





CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.7 Typical Reverse Characteristics

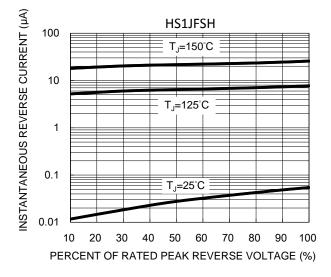
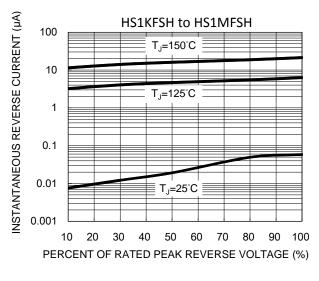


Fig.9 Typical Reverse Characteristics



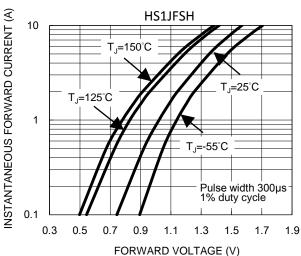
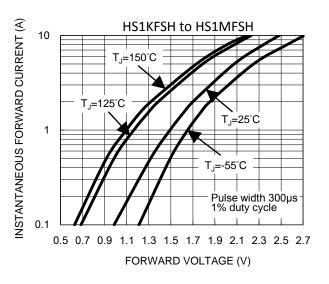


Fig.8 Typical Forward Characteristics

Fig.10 Typical Forward Characteristics



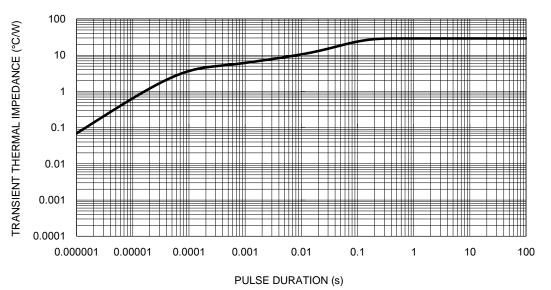


Fig.11 Typical Transient Thermal Impedance

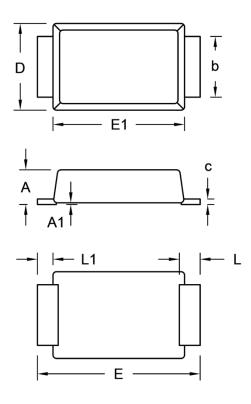


HS1DFSH – HS1MFSH Taiwan Semiconductor

PACKAGE OUTLINE DIMENSIONS

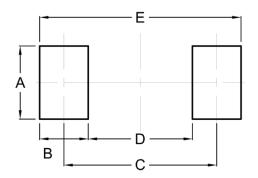
5 TAIWAN SEMICONDUCTOR

SOD-128



ми	DIM. Unit (Unit ((inch)
	Min.	Max.	Min.	Max.
A	0.90	1.10	0.035	0.043
A1	0.00	0.10	0.000	0.004
b	1.60	1.90	0.063	0.075
с	0.10	0.22	0.004	0.009
D	2.30	2.70	0.091	0.106
E	4.40	5.00	0.173	0.197
E1	3.60	4.00	0.142	0.157
L	0.40	0.80	0.016	0.031
L1	0.30	0.60	0.012	0.024

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	2.10	0.083
В	1.40	0.055
С	4.40	0.173
D	3.00	0.118
E	5.80	0.228

MARKING DIAGRAM



P/N	= Marking Code
YW	= Date Code
F	= Factory Code



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